

①

Carrier concentration.

$$n = \int Z(E) dE F(E).$$

$$= \int \frac{4\pi}{h^3} (2m)^{3/2} E^{1/2} dE \times \frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$$

$$= \frac{4\pi}{h^3} (2m)^{3/2} \int_{\text{Energy band}} E^{1/2} \frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$$

where 'T' is absolute temperature.

Density of electrons in conduction band.
(Intrinsic Semiconductor)

$$n = \int_{E_C}^{\infty} Z(E) dE F(E).$$

$$Z(E) dE = \frac{4\pi}{h^3} (2m)^{3/2} E^{1/2} dE.$$

$$m = m_e^* \quad \text{and} \quad E^{1/2} = (E - E_C)^{1/2}$$

$$\therefore n = \int_{E_C}^{\infty} \frac{4\pi}{h^3} (2m_e^*)^{3/2} (E - E_C)^{1/2} dE F(E)$$

$$F(E) = \frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$$

(2)

$$E_F = \frac{E_C + E_V}{2} \quad (\text{for intrinsic})$$

$$\therefore F(E) = \left[1 + \exp\left(\frac{E - E_F}{kT}\right) \right]^{-1}$$

$$\text{If } E - E_F \gg kT$$

$$F(E) = \exp\left(-\frac{E - E_F}{kT}\right) = \exp\left(\frac{E_F - E}{kT}\right)$$

$$\therefore n = \int_{E_C}^{\infty} \frac{4\pi}{h^3} (2m_e^*)^{3/2} (E - E_C)^{1/2} \exp\left(\frac{E_F - E}{kT}\right) dE$$

$$= \frac{4\pi}{h^3} (2m_e^*)^{3/2} \int_{E_C}^{\infty} (E - E_C)^{1/2} \exp\left(\frac{E_F - E}{kT}\right) dE$$

$$n = \frac{4\pi}{h^3} (2m_e^*)^{3/2} \exp\left(\frac{E_F}{kT}\right) \int_{E_C}^{\infty} (E - E_C)^{1/2} \exp\left(\frac{-E}{kT}\right) dE$$

To solve the above one

$$\text{Let } E - E_C = x$$

$$E = x + E_C$$

$$dE = dx$$

$$\therefore n = \frac{4\pi}{h^3} (2m_e^*)^{3/2} \exp\left(\frac{E_F - E_C}{kT}\right) \int_0^{\infty} x^{1/2} \exp\left(\frac{-x}{kT}\right) dx$$

(3) .

Using γ -function

$$\int_0^{\infty} x^{1/2} \exp\left(\frac{-x}{KT}\right) dx = (KT)^{3/2} \frac{\pi^{1/2}}{2}$$

$$\therefore n = \frac{4\pi}{h^3} (2m_e^*)^{3/2} \left(\exp \frac{E_F - E_C}{KT}\right) (KT)^{3/2} \frac{\pi^{1/2}}{2}$$

\therefore The number of electrons per unit volume in the material is given by

$$n = 2 \left(\frac{2\pi m_e^* KT}{h^2} \right)^{3/2} \exp\left(\frac{E_F - E_C}{KT}\right)$$

Calculation of density of holes.

$$P = \int_{-\infty}^{E_V} \mathcal{N}(E) dE [1 - F(E)]$$

$$\therefore P = 2 \left(\frac{2\pi m_A^* KT}{h^2} \right)^{3/2} \exp\left(\frac{E_V - E_F}{KT}\right)$$